BSS138DW

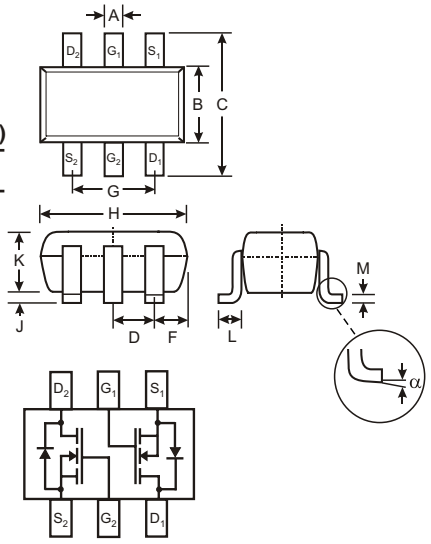
DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Available in Lead Free/RoHS Compliant Version (Note 4)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Please see Ordering Information, Note 6, on Page 2
- Terminal Connections: See Diagram
- Marking Code (See Page 2): K38
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic		Symbol	BSS138DW	Units
Drain-Source Voltage		V_{DSS}	50	V
Drain-Gate Voltage (Note 3)		V_{DGR}	50	V
Gate-Source Voltage	Continuous	V_{GSS}	±20	V
Drain Current (Note 1)	Continuous	I_D	200	mA
Total Power Dissipation (Note 1)		P_d	200	mW
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range		T_j, T_{STG}	-55 to +150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	75	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	0.5	μA	V_{DS} = 50V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	1.2	1.5	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	1.4	3.5	Ω	V_{GS} = 10V, I_D = 0.22A
Forward Transconductance	g_{FS}	100	—	—	mS	V_{DS} =25V, I_D = 0.2A, f = 1.0KHz
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	50	pF	V_{DS} = 10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	8.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	—	—	20	ns	V_{DD} = 30V, I_D = 0.2A, R_{GEN} = 50Ω
Turn-Off Delay Time	$t_{D(OFF)}$	—	—	20	ns	

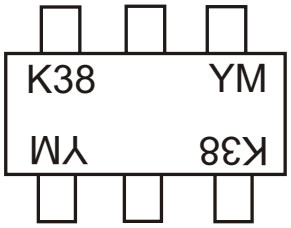
Note: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. Short duration test pulse used to minimize self-heating effect.
3. $R_{GS} \leq 20K\Omega$.
4. No purposefully added lead.

Ordering Information (Note 5)

Device	Packaging	Shipping
BSS138DW-7	SOT-363	3000/Tape & Reel

Notes: 5. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.
6. For Lead Free/RoHS Compliant version part number, please add "-F" suffix to the part number above. Example: BSS138DW-7-F.

Marking Information



K38 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

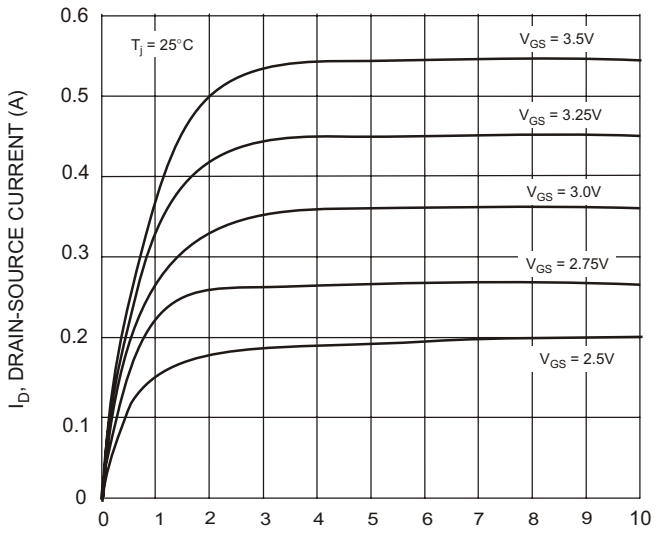


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

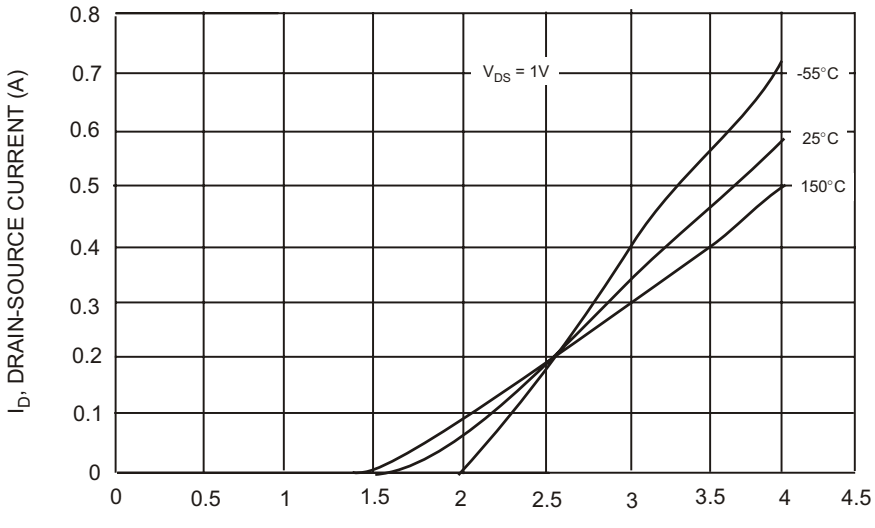


Fig. 2 Transfer Characteristics

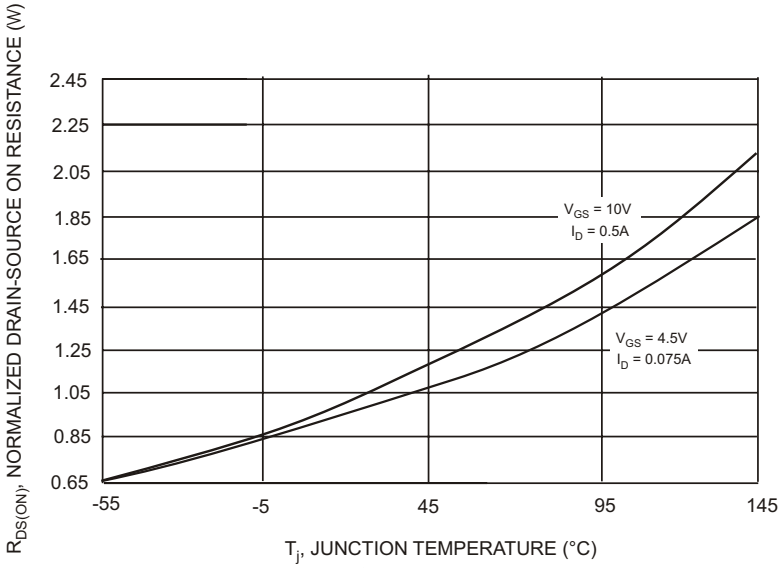


Fig. 3 Drain-Source On Resistance vs. Junction Temperature

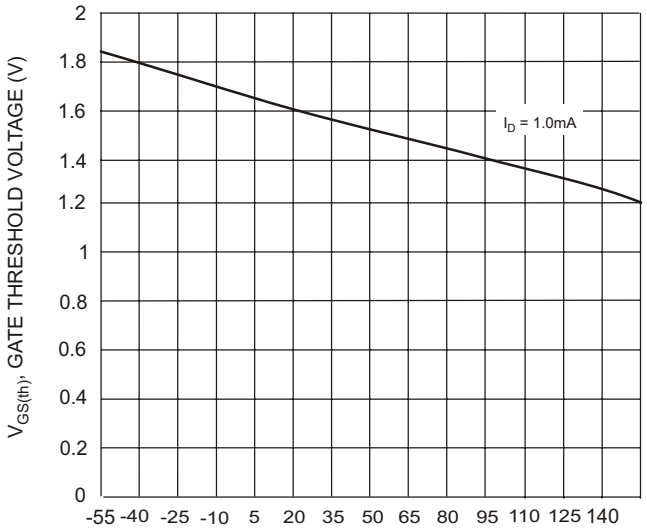


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

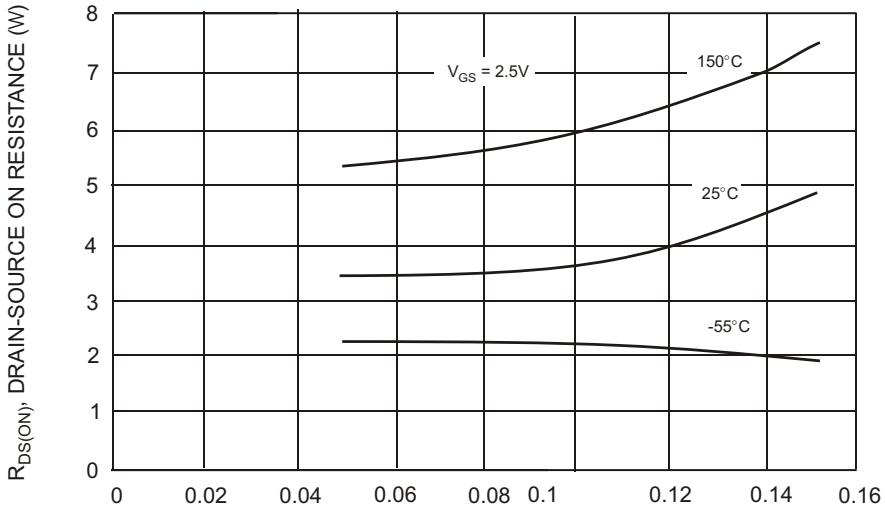


Fig. 5 Drain-Source On Resistance vs. Drain Current

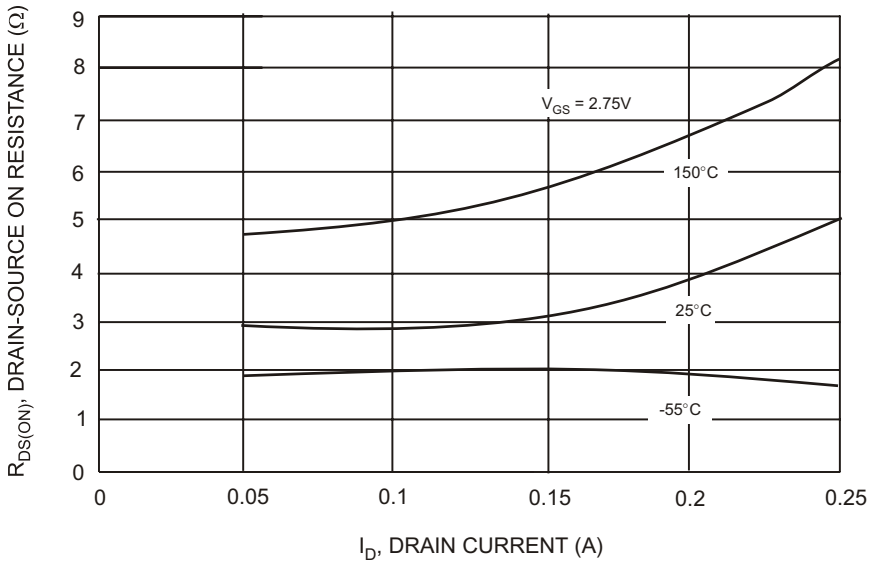


Fig. 6 Drain-Source On Resistance vs. Drain Current

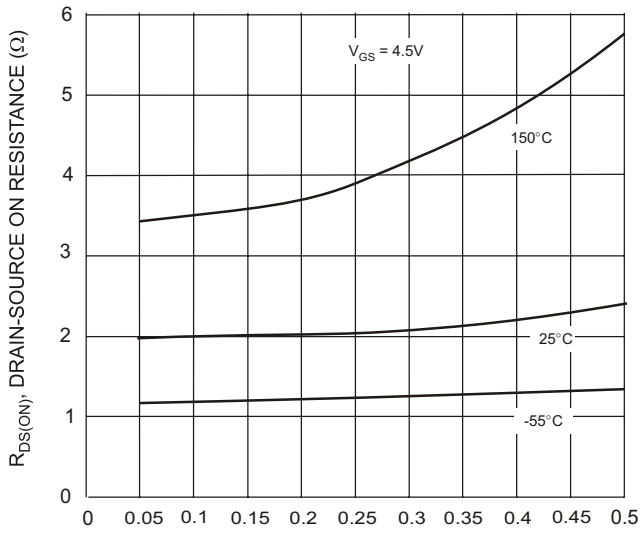


Fig. 7 Drain-Source On Resistance vs. Drain Current

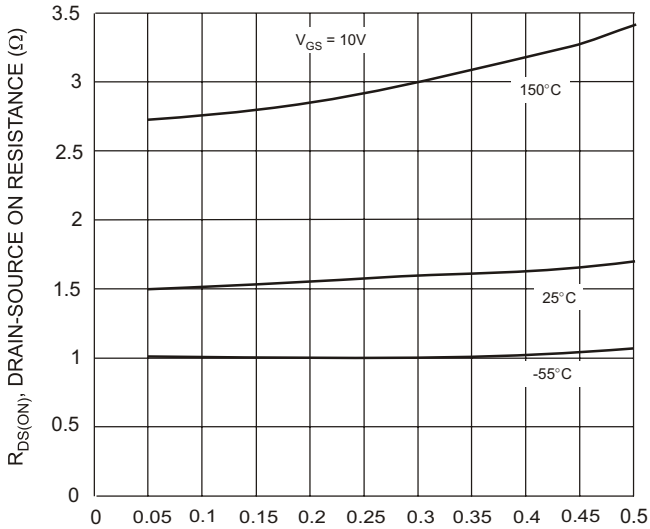


Fig. 8 Drain-Source On Resistance vs. Drain Current

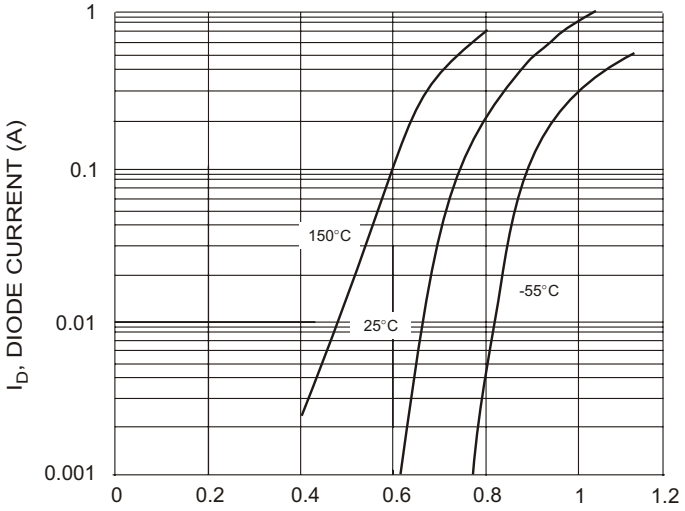


Fig. 9 Body Diode Current vs. Body Diode Voltage

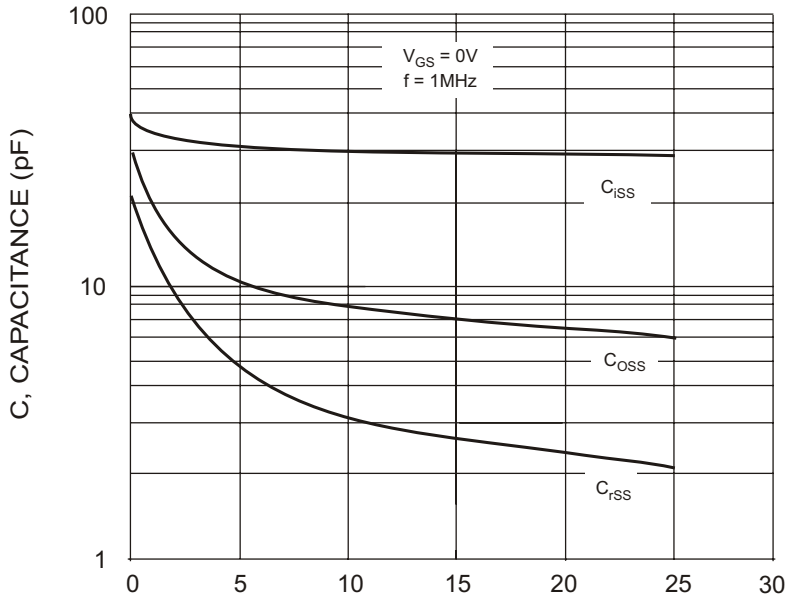


Fig. 10 Capacitance vs. Drain Source Voltage